

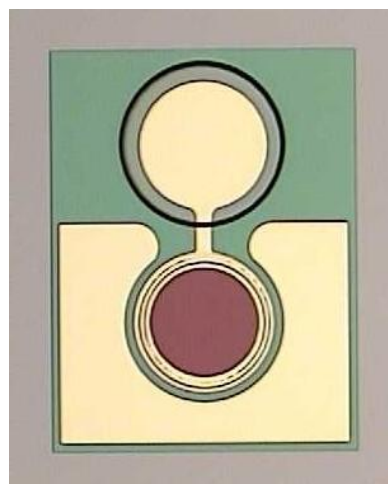
GCS InGaAs PIN Photodiodes for 1-4 Gb/sec Applications



1310/1550 nm InGaAs PIN PD

- Planar Diode on n+ InP Substrates
- Anode Bonding Pad on Front Side, Cathode on backside
- Low Dark Current & Capacitance with High Responsivity
- Bandwidths up to 4GHz
- Customer Specified Configurations Available

Part Number: Do105_68um_P2	
PHYSICAL	Typical
Aperture Dia.	68 μm
Bonding Pad Dia.	80 μm
Die Height	100-150 μm
Die Size	250 μm X 310 μm
Substrate	n+ InP



Applications

- 1.25G EPON
- Short Reach Optical Networks
- 1 to 4 Gigabit Ethernet, Fiber Channel, CATV

Key Benefits

- 4-inch Wafer Manufacturing
- Fast Cycle-Times
- CAD Support & Mask Procurement
- Robust Process

Mask ID: Do105	Conditions	Min.	Typical	Max	Unit	Notes
CHARACTERISTICS						
Bandwidth	-5V	-	4	-	GHz	
Wavelength Range	-5V	910	1310/1550	1650	nm	
Responsivity	-5V	0.8	0.9	-	A/W	@ 1310nm
Dark Current	-5V	-	0.1	1	nA	
Breakdown Voltage	-1 μA	30	-	-	V	
Capacitance	-5V	-	0.45	0.6	pF	

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